



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate DIODE

BAV99W

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 300 mA

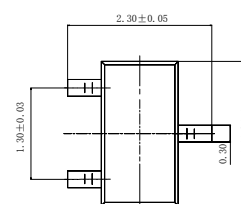
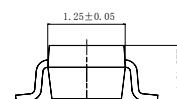
Collector-base voltage

V_R : 75 V

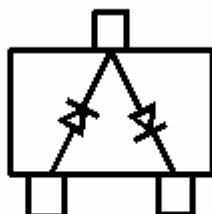
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323



Unit: mm



Marking: KJG

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 2.5\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R = 75V$ $V_R = 20V$		2.5 25	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R$ $R_L = 100\Omega$		4	nS